

Agenda

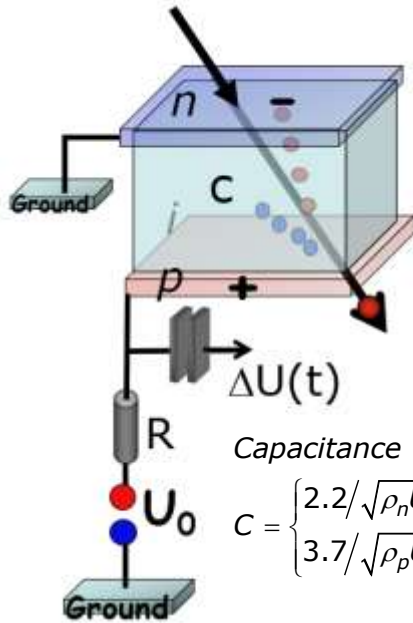
- Phenomenological model of matter ionization by particles
 - Electronic stopping
 - **Bethe-Bloch Formula**
 - Examples
 - Range and specific ionization
 - Stopping power curves, energy loss in thin foils
- Detection of ionizing radiation (photons and charged particles)
 - Gas amplification detectors (Ionization chamber, proportional counter, Geiger counter)
 - Spurious response of gas counters to photons
 - Solid-state detectors (Ge, Li surface barrier α detectors)
 - ❖ ANSEL experiment α spectroscopy
- Electronic signal processing: Detection of simultaneous emission events with multiple detectors
 - Photon spatial (angular) correlations in annihilation and nuclear γ - γ cascades
 - Coincidence measurements, electronics,
 - ❖ ANSEL PET experiment
 - Absolute activities

Reading: Knoll Chs. 11,13

Ionization Chambers (Solid-State and Gas Medium)

General principle: Radiation dissipates energy E via production of electron-ion (e^- , h^+) pairs in a medium enclosed between electrodes (Anode, Cathode). Electronic E signal picked up at A or C.

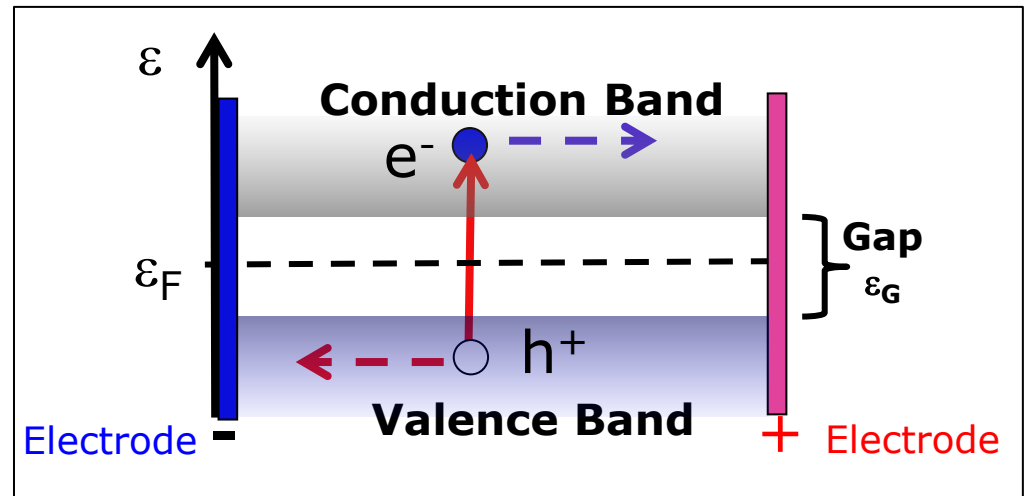
Gas volume between capacitor C electrodes.
 Energy $E \rightarrow N_{\text{ion pairs}} = E/\epsilon_{\text{ip}}(\text{gas})$



Capacitance Si :

$$C = \begin{cases} 2.2/\sqrt{\rho_n U_0} \text{ pF/mm}^2 \\ 3.7/\sqrt{\rho_p U_0} \text{ pF/mm}^2 \end{cases}$$

Semiconductor n -, p -, i -types Si, Ge, GaAs,..
→Band structure of solids VB gap CB.

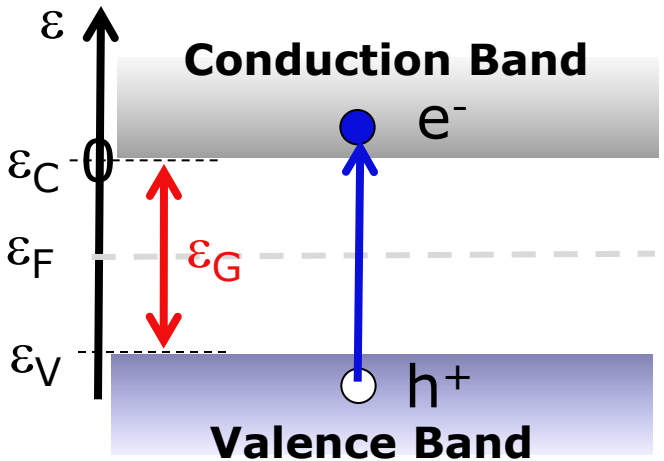


Initial (dark) state: No free charge carriers !

Ionization lifts e^- up to CB, leaves hole h^+ in VB \rightarrow free charge carriers, produce $\Delta U(t) \sim E$.

Particles and Holes in **Pure** Semi-Conductors

Fermi gas of electrons (and holes)
Fermion statistics @ temperature **T**:



$n_e, n_h = \#$ of occupied e^- or h^+ states
 $f_e, f_h \leq 1$ occupation numbers

$$n_e(\epsilon) = \frac{(2m)^{2/3} V}{2\pi^2 \hbar^3} \sqrt{\epsilon} \cdot f_e(\epsilon) \quad V = \text{volume}$$

$$n_h(\epsilon) = \frac{(2m)^{2/3} V}{2\pi^2 \hbar^3} \sqrt{|\epsilon|} \cdot f_h(\epsilon) \quad n_e = n_h !!$$

$$\epsilon_F = \epsilon_C - \epsilon_G/2 = -\epsilon_G/2 \quad \text{for } \epsilon_C := 0$$

$$f_e(\epsilon) = \left[1 + \exp\left(\frac{\epsilon - \epsilon_F}{kT}\right) \right]^{-1}$$

$$\xrightarrow{kT \approx 25 \text{ meV} \ll \epsilon_G} \exp\left(-\frac{\epsilon + \epsilon_G/2}{kT}\right)$$

$$\langle n_e^2 \rangle = \langle n_e n_h \rangle = \left(\frac{(2m)^{2/3} V}{2\pi^2 \hbar^3} \right)^2 \langle \epsilon \rangle \exp\left(-\frac{\epsilon_G}{kT}\right)$$

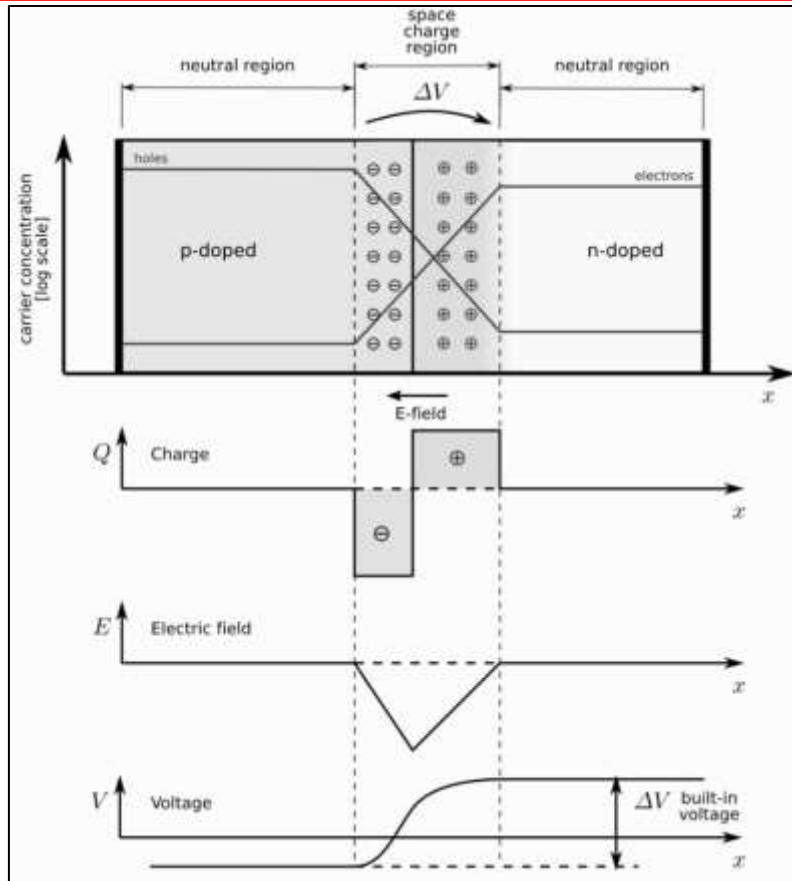
$$e^- : f_e(\epsilon) = \left[1 + \exp\left(\frac{\epsilon + \epsilon_G/2}{kT}\right) \right]^{-1}$$

$$h^+ : f_h(\epsilon) = \left[1 + \exp\left(\frac{-\epsilon + \epsilon_G/2}{kT}\right) \right]^{-1}$$

Small gaps ϵ_G (Ge) \rightarrow
high thermal currents.
Reduce by cooling.

$$\langle n_e \rangle_{rms} \sim \exp\left(-\frac{\epsilon_G}{2kT}\right) \propto \text{noise generating conductivity at } T$$

Semiconductor Junctions and Barriers

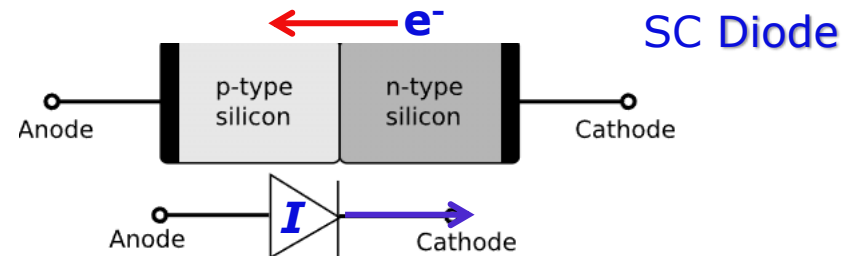


Need detector for rad-induced free charges
 → otherwise, no free carriers allowed.

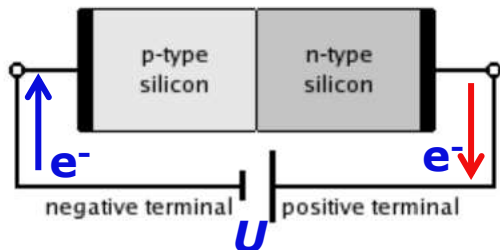
Need perfect *i*-type (intrinsic) Si = chemical Group IV with no free charge carriers.

Trick: Deplete part of combination (SC junction)
n-type Si: by doping with *Li* or Group V e^- donor atoms (*P, Sb, As*),
p-type Si: by doping with Group III e^- acceptor atoms (*B, Al, ...*).

Junctions diffuse e^- donors and acceptors into **Si** bi-layer bloc from different ends.
 Diffusion at **junction** → e^-/h^+ annihilation
 → **space charge-zone** depleted of free carriers



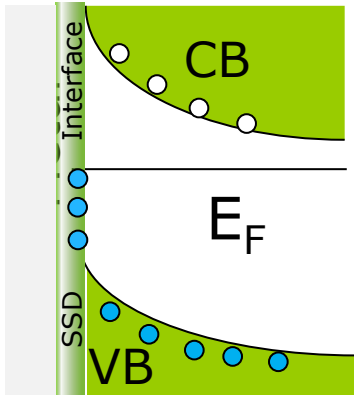
Reverse bias stabilizes depletion zone



Electrons move easily through the junction **from n to p** but **not from p to n**, and the reverse is true for holes.

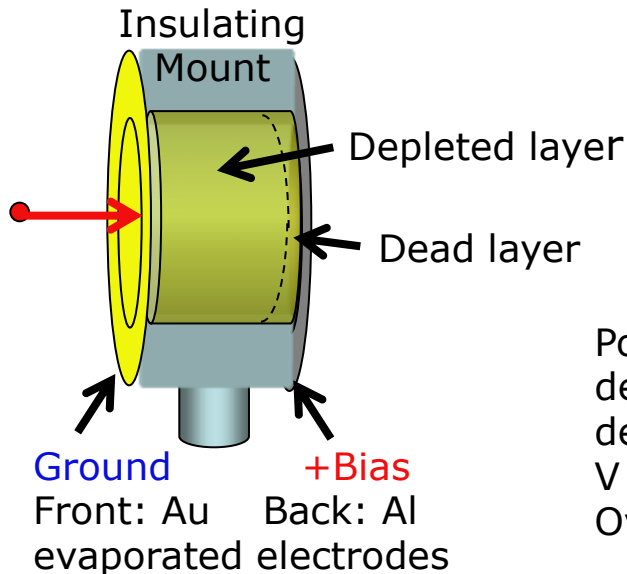
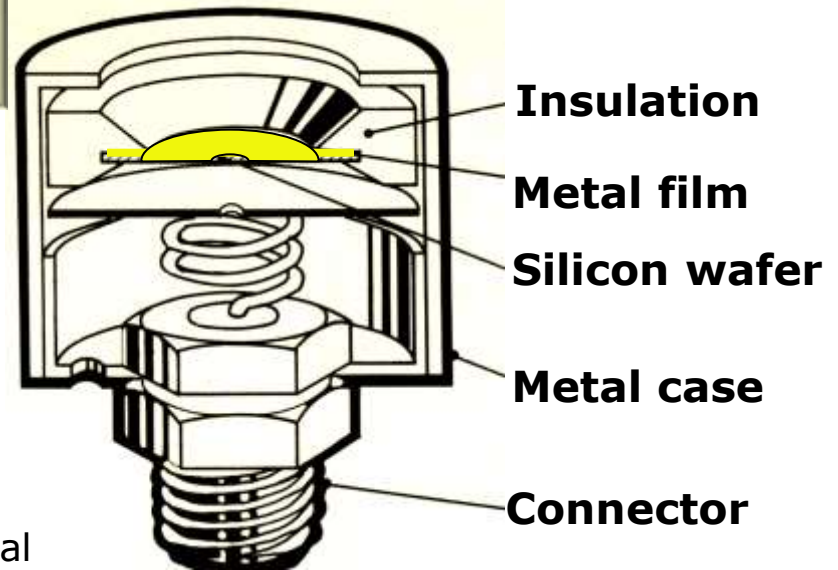
Surface Barrier Detectors

Semiconductor/ Metal Junction



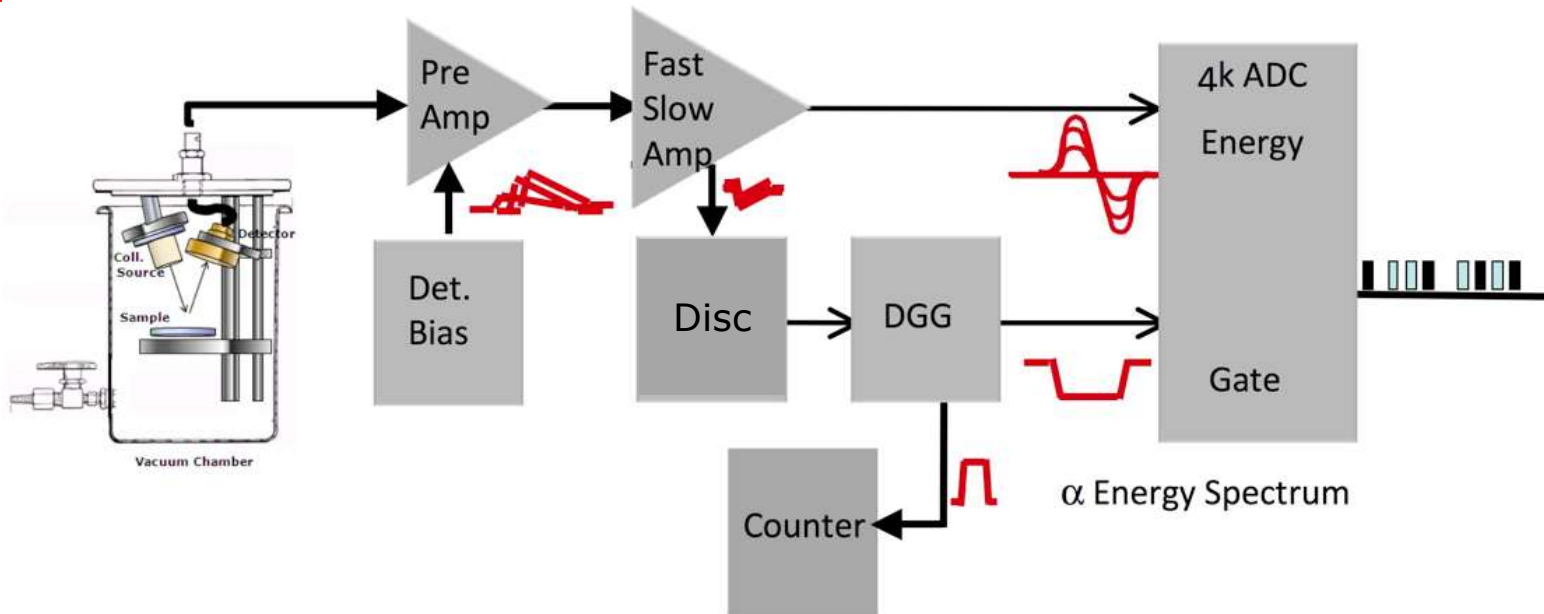
Thin metal film on Si surface produces space charge (SSD surface states) = effective barrier (contact potential) → depleted zone with no free charges. Apply reverse bias to increase depletion depth. Free charge carriers created from incident radiation → ΔV signal

ORTEC
HI/ α detector



Possible: electrical depletion depth $\sim 100\mu$
 dead layer $d_d \leq 1\mu$
 $V \sim 0.5V/\mu$
 Over-bias reduces d_d

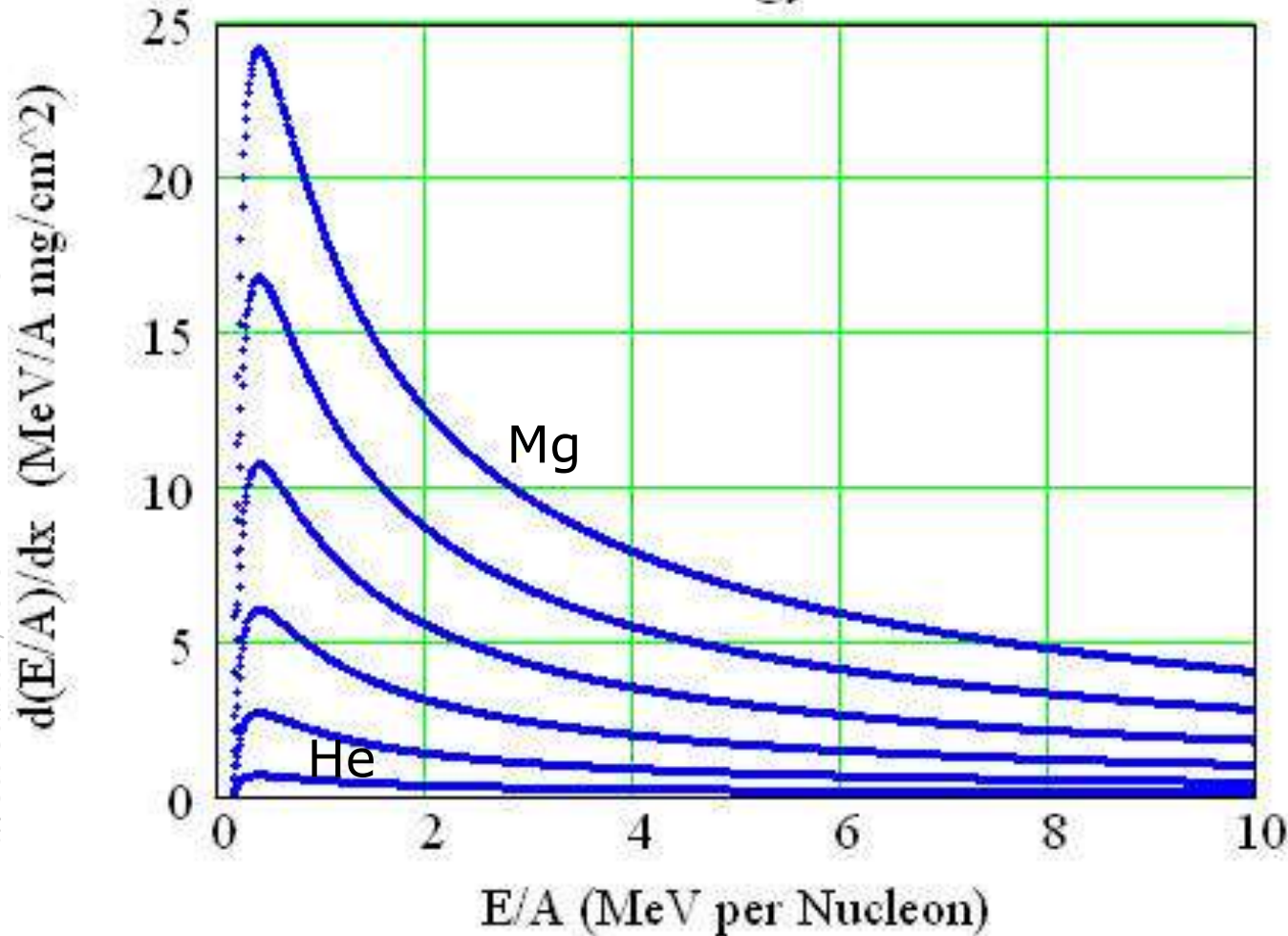
ANSEL Experiment: Alpha Spectroscopy



- Destruction-free material testing:
Use Bethe-Bloch theory to determine thickness of thin films.
(Use Rutherford-backscattering to determine material composition.)
- Demonstrate & explain interaction of particles with matter
- Calibration and optimization of signal processing of silicon detectors.
- Linearity measurements using a pulse generator.

Theoretical E-Loss in Thin Absorbers

Bethe-Bloch Energy-Loss $Z=2-12$



Units MeV/Nucleon

Loss:
 MeV/A per mg/cm^2

Bragg maximum

Semi-quantitative only: Expt values smaller both at small and large energies
→ recharging effects for projectile

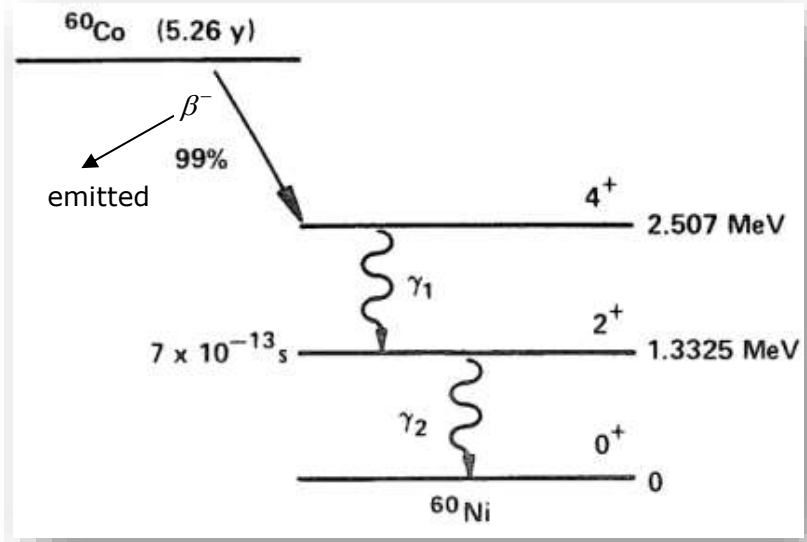
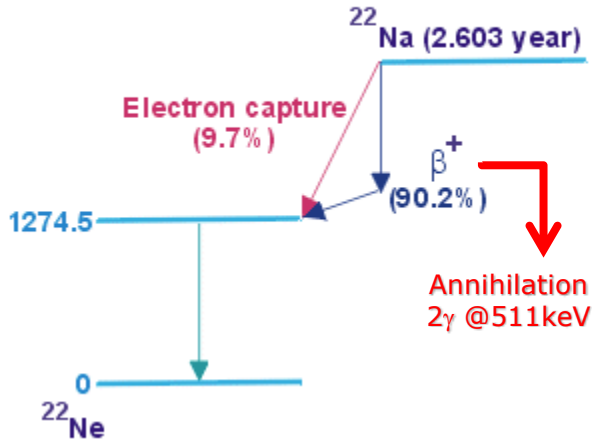
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Gamma-Gamma-Correlations

^{22}Na decay scheme



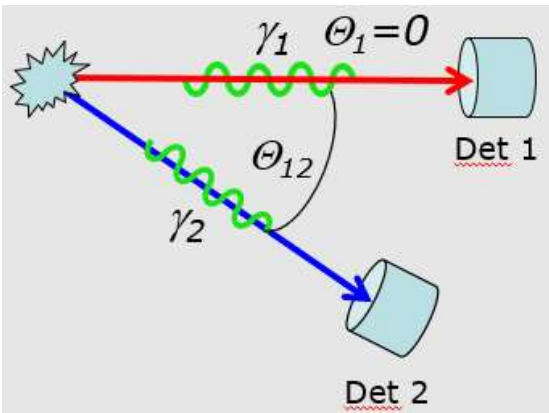
QM prediction for $P_{12}(\Theta_{12}) \rightarrow N_{phys}$

Detection probabilities

$$P_i = \varepsilon_i \cdot \frac{\Delta\Omega_i}{4\pi}; \Delta\Omega_i = \frac{F_{\text{detector } i}}{R_{\text{source-detector } i}^2}$$

Absolute Activity Measurement

2 **directionally uncorrelated** γ -rays detected as singles (\dot{N}_1 and \dot{N}_2) or coincidences (\dot{N}_{12}).

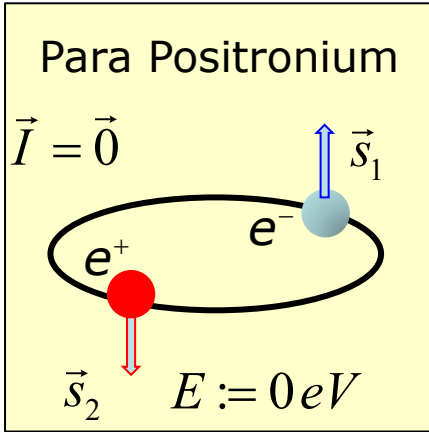


$$\begin{aligned} \dot{N}_1 &= A \cdot P_1 & \dot{N}_2 &= A \cdot P_2 & \text{individual rates} \\ P_{12} &= P_1 \cdot P_2 & \dot{N}_{12} &= A \cdot P_{12} & \text{uncorr. coinc rate} \\ A &= \frac{\dot{N}_1 \cdot \dot{N}_2}{\dot{N}_{12}} = \frac{A \cdot P_1 \cdot A \cdot P_2}{A \cdot P_{12}} & \text{singles / coinc} & & A \text{ error ??} \end{aligned}$$

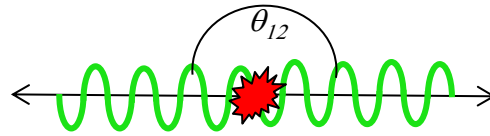
Positronium and e^+e^- Annihilation

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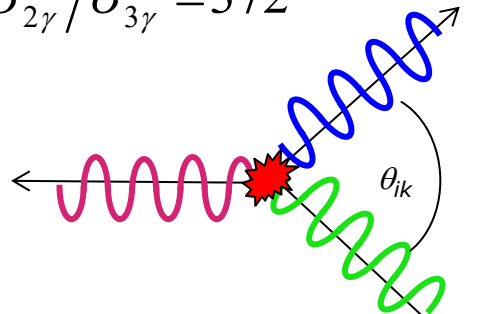
Decay at rest:
 $2E_\gamma \approx E_0 \approx 1.022 \text{ MeV}$
 2-body decay $\rightarrow \theta_{12} \approx 180^\circ$



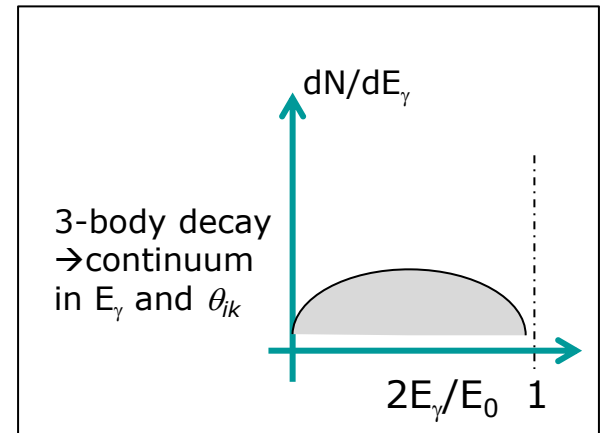
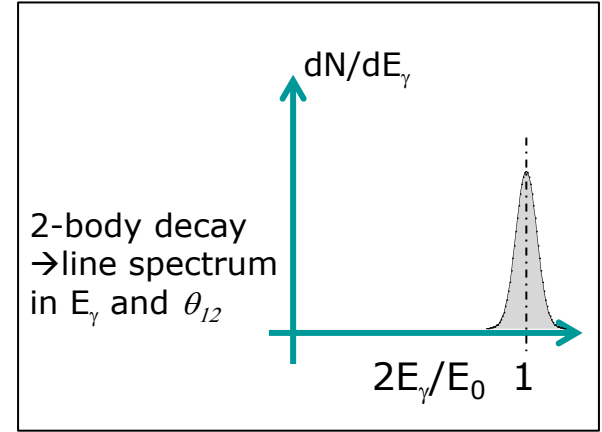
$$\tau_{2\gamma}(n) = 1.25 \cdot 10^{-10} n^3 \text{ sec}$$

$n =$ principal quantum # of positronium molecule

$$\sigma_{2\gamma} / \sigma_{3\gamma} = 372$$



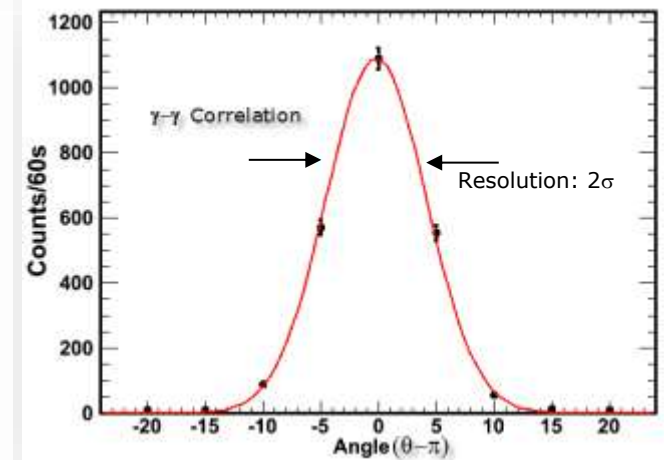
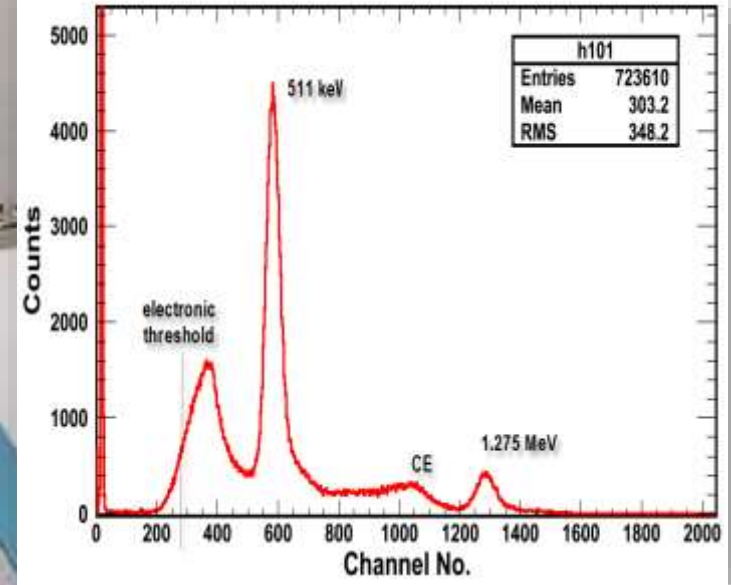
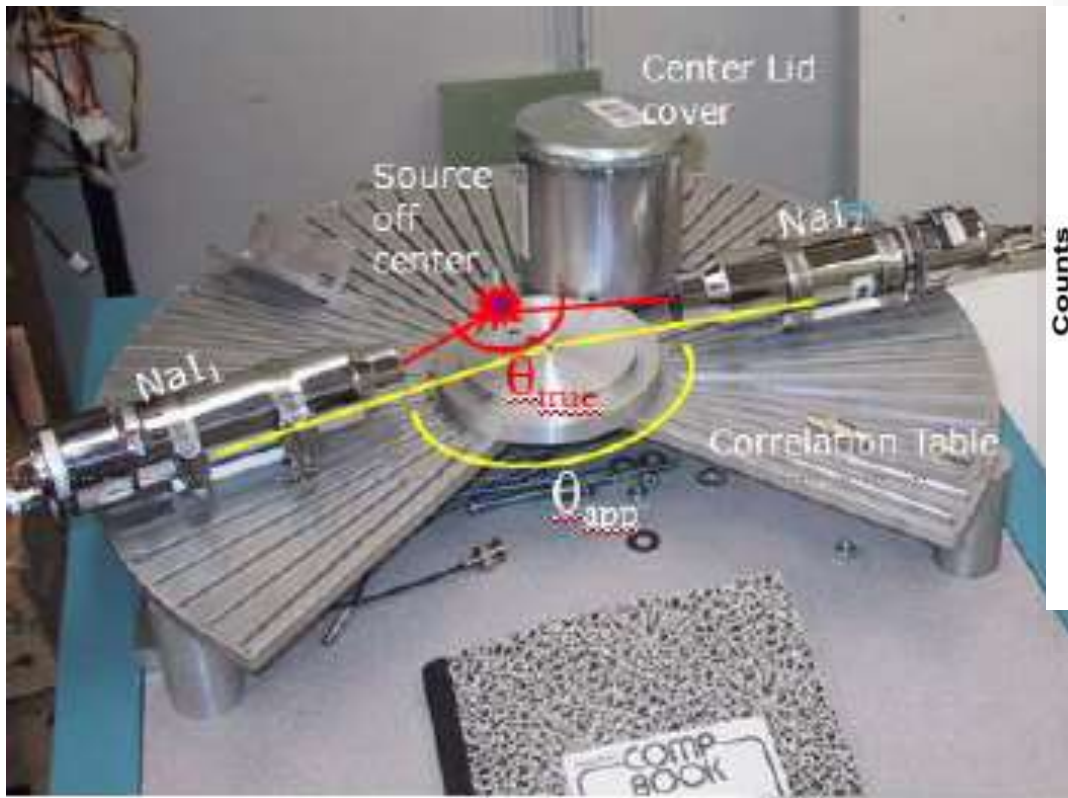
$$\tau_{3\gamma}(n) = 1.4 \cdot 10^{-7} n^3 \text{ sec}$$



$$\sigma_{2\gamma} = \pi r_0^2 \cdot \frac{v_{e^+e^-}}{c}; \quad \sigma_{2\gamma} / \sigma_{3\gamma} = 372$$

$r_0 = 2.818 \text{ fm}$, class. electron radius

ANSEL Angular Correlation Experiment



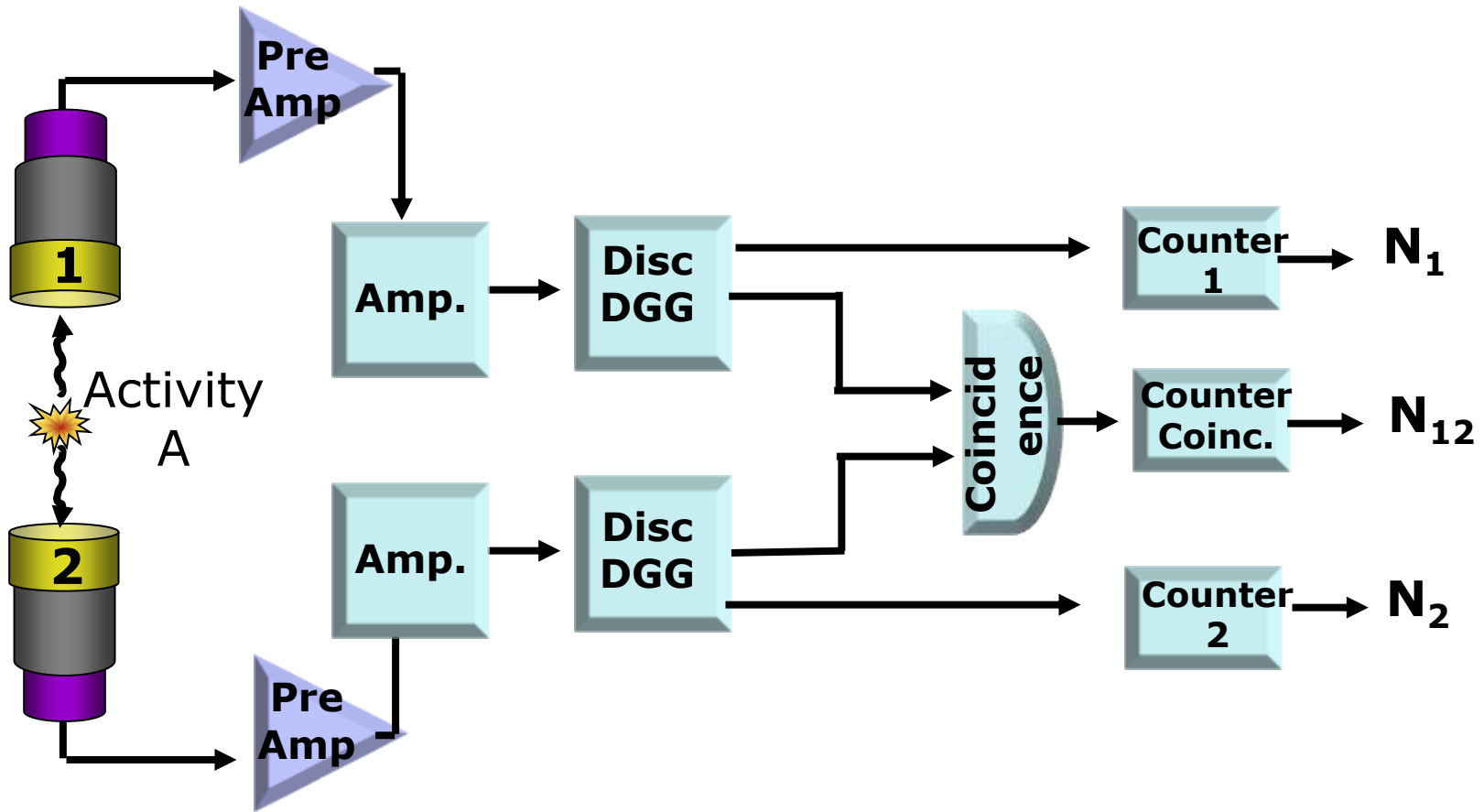
Top left: PET imaging experiment setup with two 1.5"x1.5" NaI(Tl) detectors (BICRON) on a slotted correlation table. A "point-like" ^{22}Na γ source can be hidden from view.

Top right: ^{22}Na γ spectrum measured with NaI₁.
Bottom right: γ - γ angular correlation measurement.

Second correlation setup: NaI(Tl) vs. HPGc

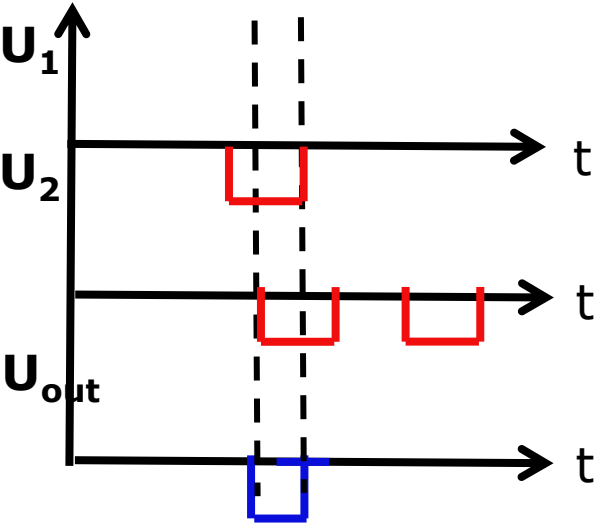
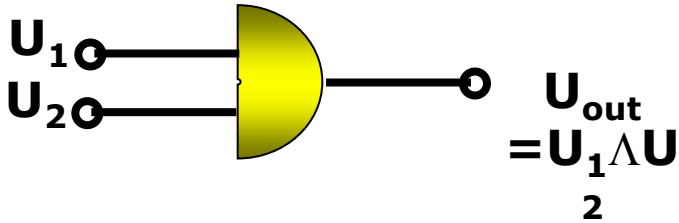
E_γ -Ungated Coincidence Measurement

Activity $A = \lambda N$ [disintegrations/time], simultaneous emission of (angular-) uncorrelated radiation types: $i = 1, 2$ per event, resp. detection probabilities P_i

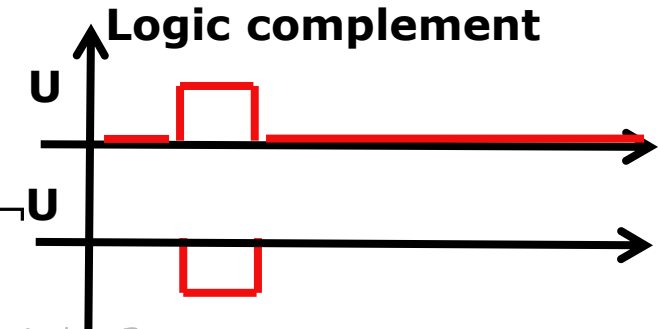


Digital Logic Modules

AND Overlap Coincidence

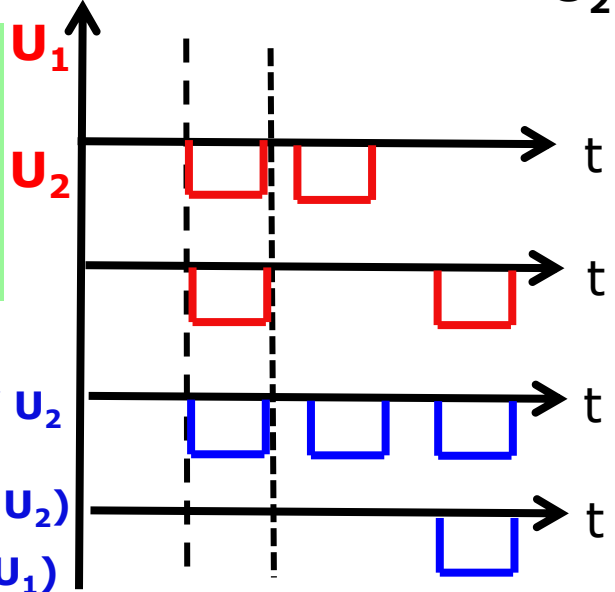
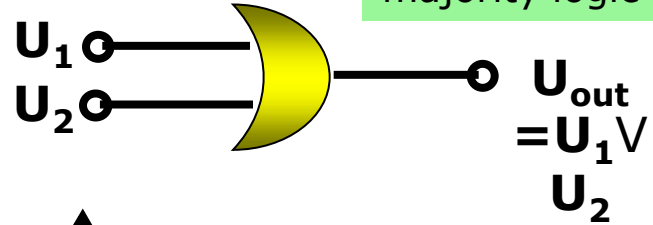


For fast timing: use fast negative logic

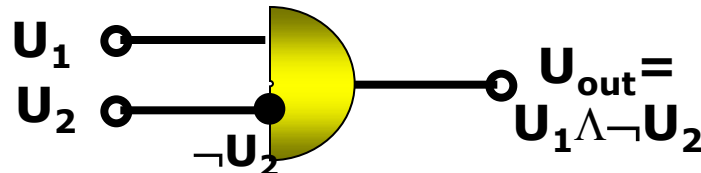


OR (inclusive)

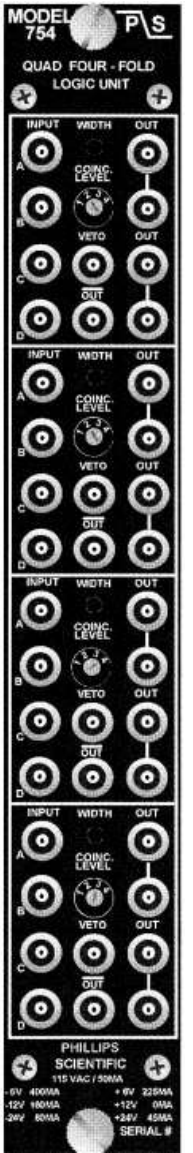
Quad 4-fold majority logic unit



incl $U_1 \vee U_2$
ex $(U_1 \vee U_2)$
 $\wedge \neg (U_2 \wedge U_1)$

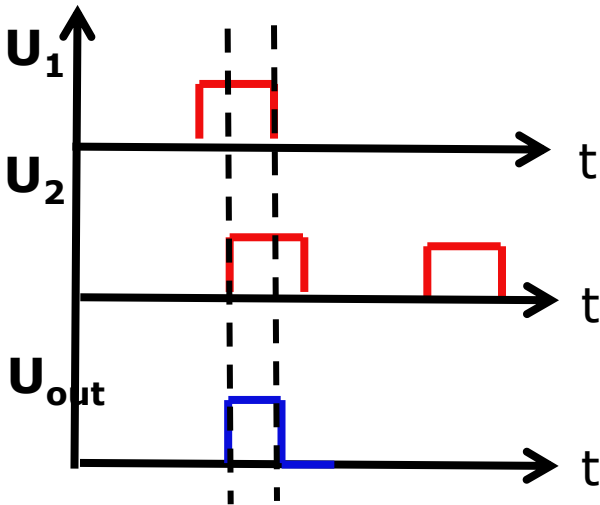
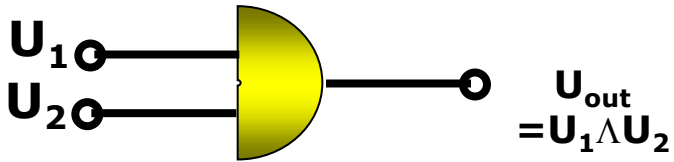


Anti-Coincidence



Digital TTL Logic Modules

AND Overlap Coincidence

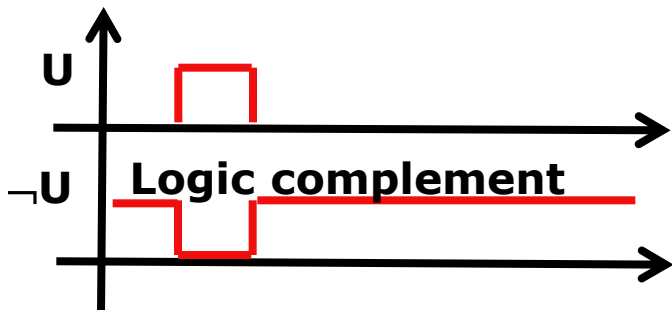


For fast timing:
use fast negative logic

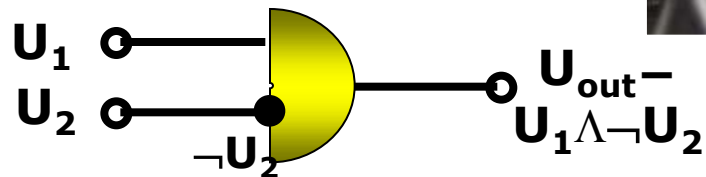
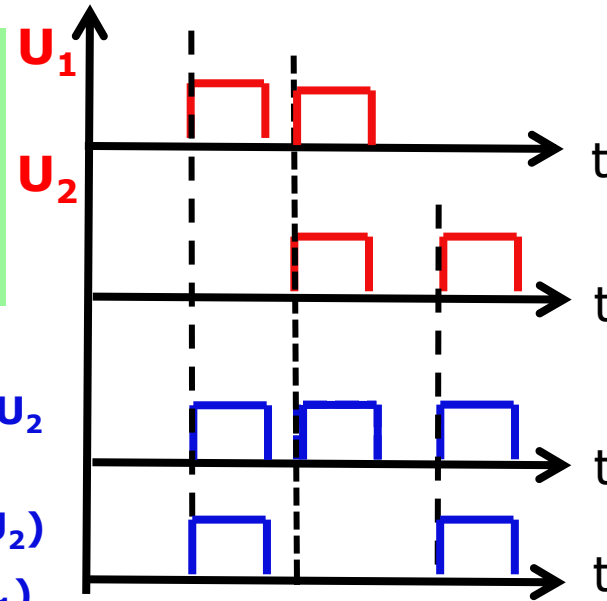
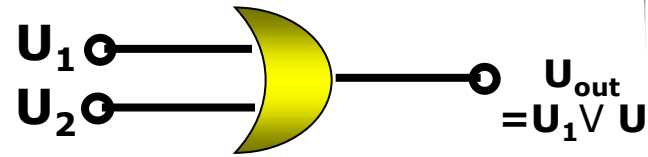
incl $U_1 \vee U_2$

ex $(U_1 \vee U_2)$

$\Lambda \neg (U_2 \wedge U_1)$



OR (inclusive)



Anti-Coincidence

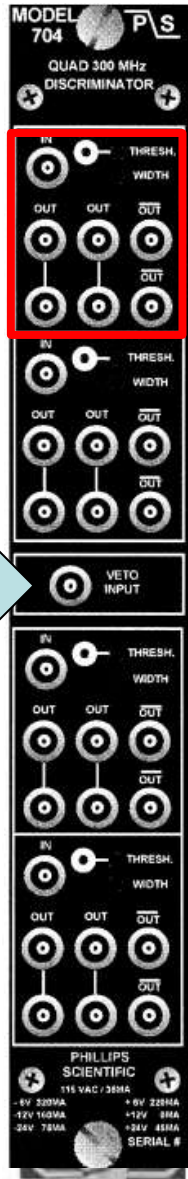
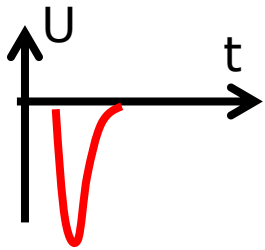
1-3 Co/Anticoincidence logic unit (TTL)



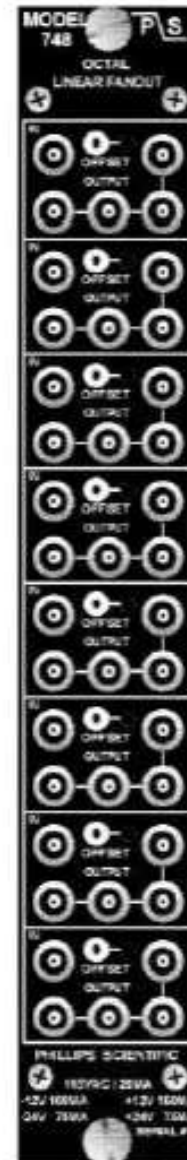
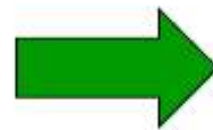
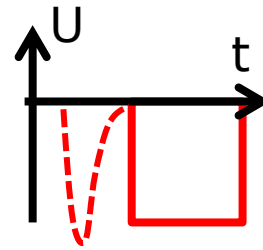
Logic Chain Elements: Fast NIM Modules

Fast LE Discriminator

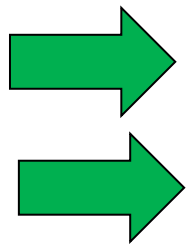
Pre/Amp



Gate & Delay Generator



Fan In/
Fan Out
Module



Input: fast, narrow NIM signal

NIM = current based logic, with negative "true"

$I = -16 \text{ mA}$

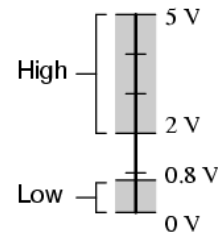
@ $50 \Omega \rightarrow -0.8 \text{ V}$

Veto

Output: Long NIM/TTL "gate" signal

Check on 50Ω termination

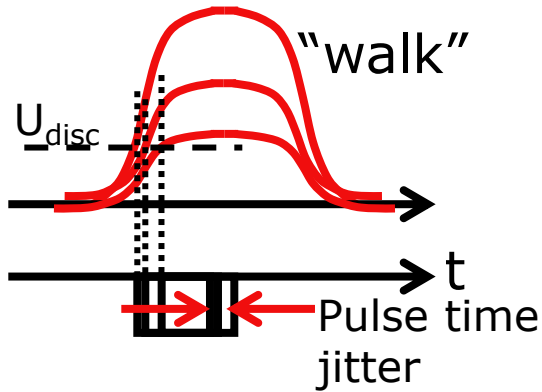
Acceptable TTL gate input signal levels



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Overlap Coincidence/ Coincidence Resolution



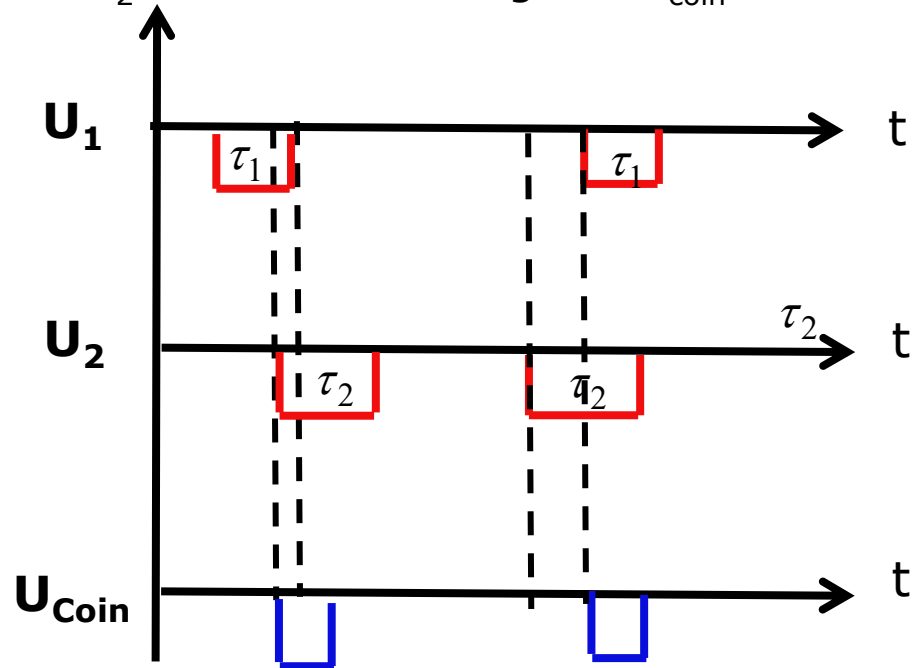
Detection of an event in detector is a stochastic process \rightarrow statistical distribution both in pulse amplitude and risetime \rightarrow time variation in crossing a discriminator threshold level. \gg Additional systematic "walk".

2 physically simultaneous events are detected in 2 counters at different times \rightarrow time jitter.

Electronic coincidence resolution time = minimum time of signal overlap.

Typical Co resolution time: $\Delta T = \tau_1 + \tau_2$

Detection of 2 instances of correlated signals U_1 and U_2 as coincidence signals U_{coin}



Digital Event Data Structure

Example of event stream with signals (observables) measured **simultaneously** in 3 inputs of the Data Acquisition Module (DDC-8),

>>>> trigger signal: inclusive OR (det1 V det2)

Sample below displays 6 successive events, 1 of them is a "coincidence."

Event#	Single event "Det 1"		Single event "Det 2"	
	Input 0 Channel #	Input 1 Channel #	Input 0 Channel #	Input 1 Channel #
51	1542		0	
52	1530		0	
53	1486		0	
54	1789		256	
55	1547		0	
56	1533		0	

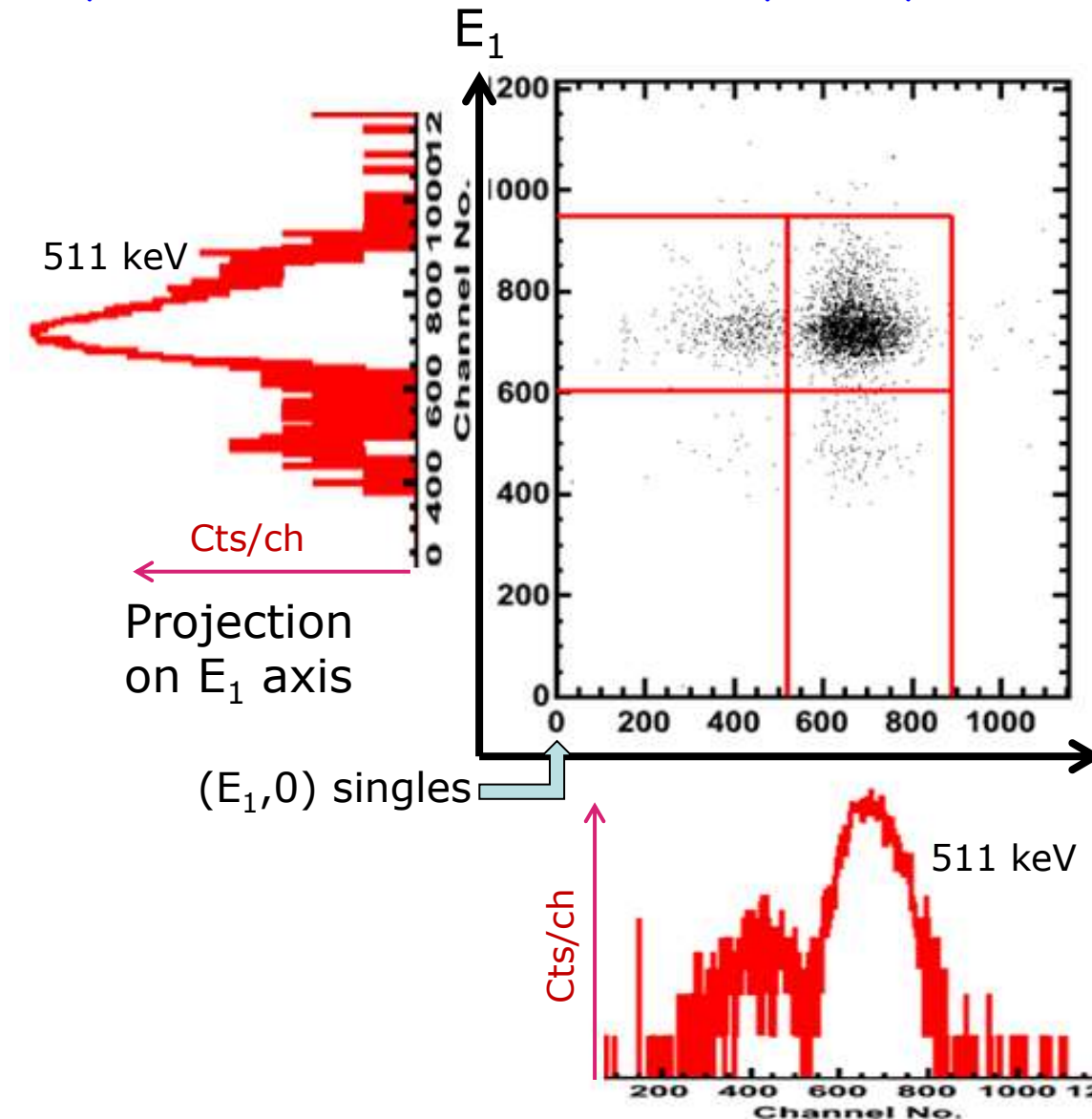
← Coincident event 0 .AND. 2

← Coincident event 0 .AND. 1

With OR trigger, coincidence "resolution" is given by slow DAQ electronics.
Fast front-end determination reduces random background.

2D Parameter Coincidence Data

Only coincident γ - γ events are accepted by DAQ.



2D Scatter Plot:

Each point represents one 2D event $\{E_1, E_2\}$

"Minimum Bias" \rightarrow
Multiplicity=2

$(0, E_2)$ singles

E_2

$(E_1, 0)$ singles

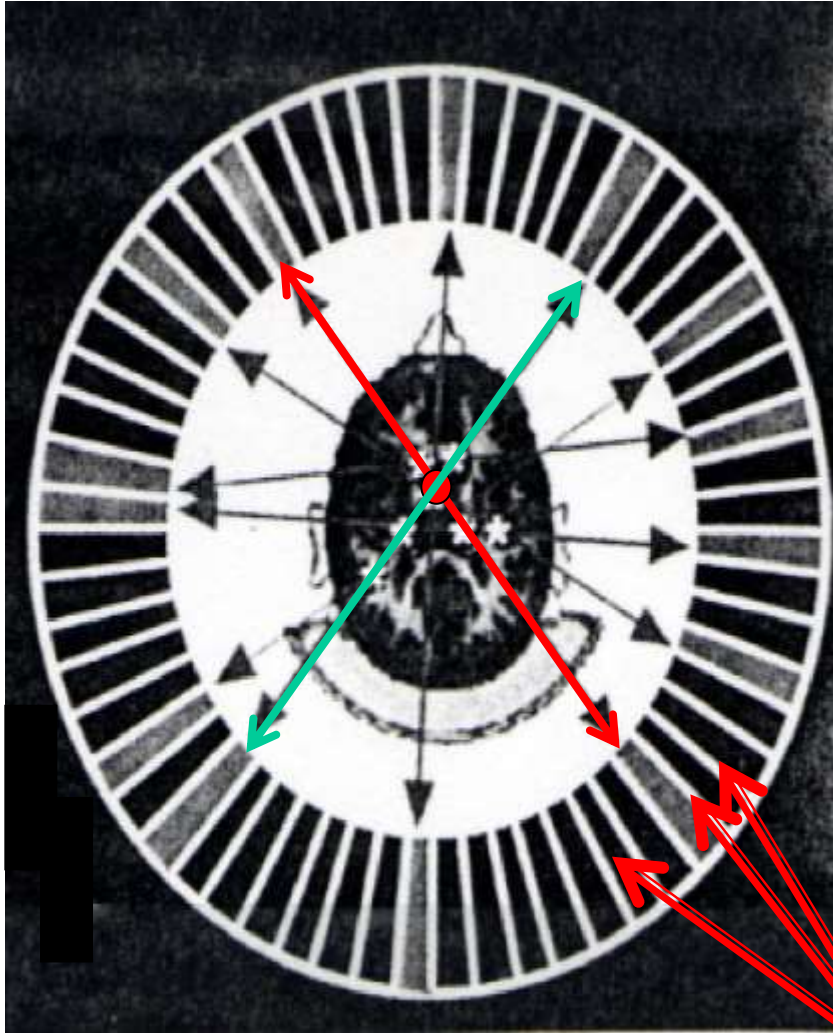
Cts/ch

511 keV

Projection on E_2 axis

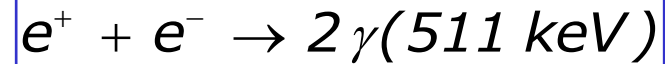
Radiation Detectors for Medical Imaging

Positron emission tomographic (PET) virtual slice through patient's brain



Administer to patient labeled tracers, e.g.,
radioactive water: H_2^{17}O
radioactive acetate: $^{11}\text{CH}_3\text{COOX}$

Observe ^{17}O or ^{11}C β^+ decay
mostly via β^+ annihilation



Positron e^+ (anti-matter) annihilates with electron e^- (its matter equivalent of the same mass) to produce pure energy (photons, γ -rays). Energy and momentum balance require back-to-back (180°) emission of 2 γ -rays of equal energy

γ Detectors (e.g., NaI(Tl) ,...)